

High-speed Switching Transistor (–60V, –5A)

2SA1952

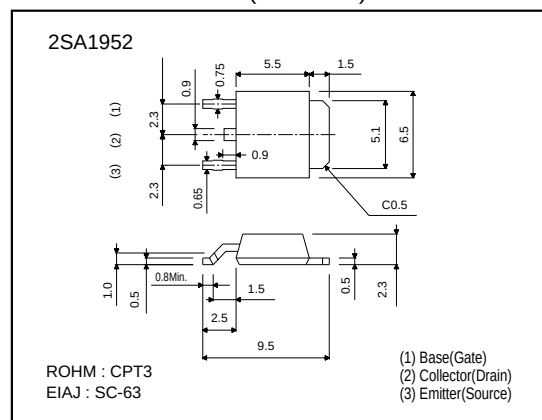
●Features

- 1) High speed switching. (t_f : Typ. 0.15 μ s at $I_C = -3A$)
- 2) Low $V_{CE(sat)}$. (Typ. –0.2V at $I_C/I_B = -3/-0.15A$)
- 3) Wide SOA. (safe operating area)
- 4) Complements the 2SC5103.

●Absolute maximum ratings ($T_a = 25^\circ C$)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V_{CBO}	–100	V
Collector-emitter voltage	V_{CEO}	–60	V
Emitter-base voltage	V_{EBO}	–5	V
Collector current	I_C	–5	A
		–10	A(Pulse)
Collector power dissipation	P_C	1	W
		10	W($T_C = 25^\circ C$)
Junction temperature	T_j	150	$^\circ C$
Storage temperature	T_{stg}	–55–+150	$^\circ C$

●External dimensions (Units : mm)



●Packaging specifications and h_{FE}

Type	2SA1952
Package	CPT3
h_{FE}	Q
Code	TL
Basic ordering unit (pieces)	2500

●Electrical characteristics ($T_a = 25^\circ C$)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	–100	–	–	V	$I_C = -50\mu A$
Collector-emitter breakdown voltage	BV_{CEO}	–60	–	–	V	$I_C = -1mA$
Emitter-base breakdown voltage	BV_{EBO}	–5	–	–	V	$I_E = -50\mu A$
Collector cutoff current	I_{CBO}	–	–	–10	μA	$V_{CB} = -100V$
Emitter cutoff current	I_{EBO}	–	–	–10	μA	$V_{EB} = -5V$
Collector-emitter saturation voltage	$V_{CE(sat)}$	–	–	–0.3	V	$I_C/I_B = -3A/-0.15A$
		–	–	–0.5	V	$I_C/I_B = -4A/-0.2A$
		–	–	–1.2	V	$I_C/I_B = -3A/-0.15A$
Base-emitter saturation voltage	$V_{BE(sat)}$	–	–	–1.5	V	$I_C/I_B = -4A/-0.2A$
		–	–	–	V	$V_{CE} = -2V, I_C = -1A$
DC current transfer ratio	h_{FE}	120	–	270	–	$V_{CE} = -10V, I_E = 0.5A, f = 30MHz$
Transition frequency	f_T	–	80	–	MHz	$V_{CB} = -10V, I_E = 0A, f = 1MHz$
Output capacitance	C_{ob}	–	130	–	pF	$I_C = -3A, R_L = 10\Omega$
Turn-on time	t_{on}	–	–	0.3	μs	$I_{B1} = -I_{B2} = -0.15A$
Storage time	t_{stg}	–	–	1.5	μs	$V_{CC} = -30V$
Fall time	t_f	–	–	0.3	μs	